

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/707084	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 15:52
L2	42	(US-20030218183-\$ or US-20030146444-\$ or US-20050012113-\$ or US-20020074553-\$ or US-20040080010-\$ or US-20030062525-\$ or US-20030015708-\$ or US-20020155634-\$ or US-20050167680-\$ or US-20060199289-\$ or US-20060226417-\$ or US-20050274964-\$ or US-20050082543-\$ or US-20050167697-\$ or US-20040124435-\$ or US-20030127658-\$ or US-20030071276-\$ or US-20020096687-\$ or US-20030214807-\$ or US-20030047744-\$ or US-20030122147-\$).did. or (US- 6429467-\$ or US- 6208074-\$ or US- 5717235-\$ or US- 5977565-\$ or US- 5673220-\$ or US- 5932905-\$ or US- 5507881-\$ or US- 5707887-\$ or US- 5847397-\$ or US- 5677538-\$ or US- 5598014-\$ or US- 6586272-\$ or US- 6495852-\$ or US- 6455340-\$ or US- 7151281-\$).did. or (JP-06216404-\$).did. or (US-20050012113-\$ or US-20030230235-\$ or EP-296371-\$ or US-20050032345-\$ or JP-06216404-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2008/03/10 16:06

L3	18	I2 and schottky	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:06
L4	0	I2 and (schottky near10 biased)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:07
L5	5	I2 and (schottky near10 (bias or biasing or biased))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:07
L6	5	I2 and (schottky with (bias or biasing or biased))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:07
L7	6	I2 and (schottky with (reverse or bias or biasing or biased))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:08
L8	3	I2 and (schottky near contact) with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:14
L9	0	I2 and (schottky near contact) with electrode with (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:15
L10	1	I2 and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:15
L11	1	I2 and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:15
L12	167	(schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:17

L13	0	photodetecotr and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:18
L14	4	photodetector and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:18
L15	1	photodetector and (gan or nitride) and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:18
L16	75	(gan or nitride) and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:19
L17	44	(gan or (gallium near nitride)) and (schottky near contact) with electrode same (reverse or forward)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:19
L18	162	(gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:19
L19	162	(gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:20
L20	69	(gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward) same (bias or biasing or baised))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:20
L21	83	(gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward) same (bias or biasing or biased))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:20

L22	24	(gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:22
L23	18	(gan or (gallium near nitride)).clm. and (schottky with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:24
L24	0	(gan or (gallium near nitride)).clm. and (schottky with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:24
L25	0	(gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:24
L26	2	(gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:24
L27	27	(gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode with (gan or (gallium near nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:25

L28	4	(gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode with (gan or (gallium near nitride))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:25
L29	34	(gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:26
L30	1	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near2 between)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:27
L31	25	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near2 between))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:27
L32	30	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:27
L33	3	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:28
L34	30	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:29
L35	0	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between) with ((high-resistivity) or resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:29

L36	0	(gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between) same ((high-resistivity) or resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:29
L37	1	(gan or (gallium near nitride)).clm. and ((schottky near contact) same (electrode near5 between) same ((high-resistivity) or resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:30
L38	398	((schottky near contact) with (electrode near5 between))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:30
L39	1	((schottky near contact) with (electrode near5 between)) and ((high near resistivity) near2 ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:31
L40	3	((schottky near contact) with (electrode near5 between)) and (((high near resistivity) or resistive or resistivity) near2 ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:31
L41	3	((schottky near contact) with (electrode near5 between)) and (((highly or high) near resistivity) or resistive or resistivity) near2 ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:32
L42	5	((schottky near contact) with (electrode near5 between) near5 ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:33

L43	44	((schottky near contact) with (electrode) near10 ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:33
L44	56	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:34
L45	16	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:38
L46	2	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) same (leakage near current)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:39
L47	3	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) and (leakage near current)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:39
L48	17	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) and (leakage near current))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:40
L49	6	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) same (leakage near current))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:40
L50	5	((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) same (leakage near current) same reverse)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:41

L51	34373	((schottky near contact) near10 (electrode) near10 (gallium adj nitride) or gan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:42
L52	37	((schottky near contact) near10 (electrode) near10 ((gallium adj nitride) or gan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:42
L53	13	((schottky near contact) near10 (electrode) near10 ((gallium adj nitride) or gan)) and leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 16:42
L54	98	(US-20030218183-\$ or US-20030146444-\$ or US-20050012113-\$ or US-20020074553-\$ or US-20040080010-\$ or US-20030062525-\$ or US-20030015708-\$ or US-20020155634-\$ or US-20050167680-\$ or US-20060199289-\$ or US-20060226417-\$ or US-20050274964-\$ or US-20050082543-\$ or US-20050167697-\$ or US-20040124435-\$ or US-20030127658-\$ or US-20030071276-\$ or US-20020096687-\$ or US-20030214807-\$ or US-20030047744-\$ or US-20030122147-\$ or US-20070066020-\$ or US-20050194612-\$ or US-20060054925-\$ or US-20040144991-\$ or US-20080038856-\$).did. or (US-20070228415-\$ or US-20070194347-\$ or US-20070187666-\$ or US-20070170934-\$ or US-20070166888-\$ or US-20070147453-\$ or US-20070145390-\$ or US-20070085097-\$ or US-20070026552-\$ or US-20060226442-\$ or US-20060226415-\$ or US-20060223293-\$ or US-	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2008/03/10 17:28

20050151255-\$ or US-
20050087766-\$ or US-
20050051804-\$ or US-
20040266043-\$ or US-
20040201038-\$ or US-
20040173751-\$ or US-
20040127042-\$ or US-
20030205721-\$ or US-
20030183921-\$ or US-
20020179932-\$ or US-
20020179914-\$ or US-
20020017696-\$ or US-
20010042860-\$ or US-
20010040247-\$ or US-
20010040246-\$).did.
or (US-6429467-\$ or
US-6208074-\$ or US-
5717235-\$ or US-
5977565-\$ or US-
5673220-\$ or US-
5932905-\$ or US-
5507881-\$ or US-
5707887-\$ or US-
5847397-\$ or US-
5677538-\$ or US-
5598014-\$ or US-
6586272-\$ or US-
6495852-\$ or US-
6455340-\$ or US-
7151281-\$ or US-
4696648-\$ or US-
4593304-\$ or US-
7002189-\$ or US-
7329908-\$ or US-
7285806-\$ or US-
7224004-\$ or US-
7205168-\$ or US-
7132699-\$ or US-
7071526-\$ or US-
6969873-\$ or US-
6965107-\$).did. or
(US-6890834-\$ or US-
6703649-\$ or US-
6593597-\$ or US-
6552373-\$ or US-
6492669-\$ or US-
6350999-\$ or US-
6064082-\$).did. or
(JP-06216404-\$ or JP-
01253286-\$ or JP-
2004228481-\$ or JP-
2003229566-\$ or JP-
2000223697-\$).did. or
(US-20050012113-\$
or US-20030230235-\$

		or EP-296371-\$ or US-20050032345-\$ or JP-06216404-\$ or KR-587021-B-\$ or KR-609968-B-\$ or CN-1641327-\$ or US-20040080011-A-\$ or JP-2001185717-\$). did.				
L55	69	I54 and (schottky near contact)\	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:28
L56	69	I54 and (schottky near contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:28
L57	63	I54 and ((schottky near contact) same (gan or (gallium near nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:29
L58	61	I54 and ((schottky near contact) with (gan or (gallium near nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:29
L59	53	I54 and ((schottky near contact) with (gan or (gallium near nitride)) with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:29
L60	5858	schottky near barrier near diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:37
L61	9	I54 and schottky near barrier near diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:37
L62	9	I54 and ((schottky near barrier near diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:38

L63	99	nucleation and ((schottky near barrier near diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:38
L64	85	nucleation and active and ((schottky near barrier near diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:38
L65	13	nucleation and active and (schottky near contact) and ((schottky near barrier near diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:38
L66	230	active and (schottky near contact) and ((schottky near barrier near diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:39
L67	102	active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:40
L68	19	active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (leakage near current) and (gan or (gallium near nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:40
L69	36	active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (gan or (gallium near nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:41
L70	5	active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (gan or (gallium near nitride)) and ((high or highly) near (resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:42

L71	10	(schottky near contact) and ((schottky near barrier near diode) or sbd) and (gan or (gallium near nitride)) and ((high or highly) near (resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:42
L72	45	(schottky near contact) and ((schottky near2 diode) or sbd) and (gan or (gallium near nitride)) and ((high or highly) near (resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:43
L73	29	(schottky near contact) and ((schottky near2 diode) or sbd) and (gan or (gallium near nitride)).clm. and ((high or highly) near (resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:44
L74	11	(schottky near contact).clm. and ((schottky near2 diode) or sbd) and (gan or (gallium near nitride)).clm. and ((high or highly) near (resistive or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:44
L75	1676	(schottky near2 diode) and (schottky near contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:45
L76	273	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:45
L77	222	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:45

L78	179	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 17:45
L79	97	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near2 gallium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:09
L80	65	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near2 gallium)) and ((gan or gallium) with (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:10
L81	85	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near2 gallium)) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:12

L82	87	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near5 gallium)) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:12
L83	12	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near5 gallium)) and ((gan or gallium) same (dope or doping or doped or dopant)) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:12
L84	17	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:13

L85	134	(schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:21
L86	139	(schottky near2 diode) and (schottky adj (metal or contact)) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:23
L87	52	(schottky near2 diode) and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:23
L88	40	(schottky near2 diode) and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:23

L89	20	(schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:24
L90	8	(schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:25
L91	4	(schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and (resistive or resistivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:26

L92	8	(schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:26
L93	9	(schottky near2 diode) and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:28
L94	10	(schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:29

L95	10	(schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact). ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)). clm. and leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:29
L96	10	(schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact). ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).ti, ab,clm. and leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:32
L97	4	(schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact). ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).ti, ab,clm. and leakage and electrode.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:32

L98	1	(schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact).ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).ti,ab,clm. and leakage.ti,ab,clm. and electrode.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:32
L99	19710	((schottky near2 diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:34
L100	2617	((schottky near2 diode) or sbd) and (ohmic near contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:35
L101	935	((schottky near2 diode) or sbd) and (ohmic near contact) and (schottky adj (metal or contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:35
L102	930	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:35
L103	32	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and (aluminum near2 indium near2 gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:35

L104	23	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and ((aluminum near2 indium near2 gallium near2 nitride) and alingan or inalgan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:36
L105	47	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and ((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:36
L106	10	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and (((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) same schottky)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:37
L107	5	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) same schottky)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:38
L108	4	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) same (schottky adj contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:38

L109	826	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:39
L110	667	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (dope or doping or doped or dopant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:39
L111	34	((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (dope or doping or doped or dopant) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:39
L112	17	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)) and (dope or doping or doped or dopant) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:40
L113	12	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:40
L114	9	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:40

L115	135	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:40
L116	49	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:51
L117	47	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) same (schottky adj contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:57
L118	44	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) same (schottky adj contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:58

		same (metal or electrode))				
L119	39	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) with (schottky adj contact) same (metal or electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:58
L120	30	((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) with (schottky adj contact) with (metal or electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 18:58
L121	105	(US-20030218183-\$ or US-20030146444-\$ or US-20050012113-\$ or US-20020074553-\$ or US-20040080010-\$ or US-20030062525-\$ or US-20030015708-\$ or US-20020155634-\$ or US-20050167680-\$ or US-20060199289-\$ or US-20060226417-\$ or US-20050274964-\$ or US-20050082543-\$ or US-20050167697-\$ or US-20040124435-\$ or US-20030127658-\$	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2008/03/10 19:01

or US-20030071276-\$
or US-20020096687-\$
or US-20030214807-\$
or US-20030047744-\$
or US-20030122147-\$
or US-20070066020-\$
or US-20050194612-\$
or US-20060054925-\$
or US-20040144991-\$
or US-20080038856-\$).did. or (US-
20070228415-\$ or US-
20070194347-\$ or US-
20070187666-\$ or US-
20070170934-\$ or US-
20070166888-\$ or US-
20070147453-\$ or US-
20070145390-\$ or US-
20070085097-\$ or US-
20070026552-\$ or US-
20060226442-\$ or US-
20060226415-\$ or US-
20060223293-\$ or US-
20050151255-\$ or US-
20050087766-\$ or US-
20050051804-\$ or US-
20040266043-\$ or US-
20040201038-\$ or US-
20040173751-\$ or US-
20040127042-\$ or US-
20030205721-\$ or US-
20030183921-\$ or US-
20020179932-\$ or US-
20020179914-\$ or US-
20020017696-\$ or US-
20010042860-\$ or US-
20010040247-\$ or US-
20010040246-\$).did.
or (US-20060094145-\$
or US-20050202661-\$
or US-20040119063-\$
or US-20010034116-\$).did. or (US-
6429467-\$ or US-
6208074-\$ or US-
5717235-\$ or US-
5977565-\$ or US-
5673220-\$ or US-
5932905-\$ or US-
5507881-\$ or US-
5707887-\$ or US-
5847397-\$ or US-
5677538-\$ or US-
5598014-\$ or US-
6586272-\$ or US-

		6495852-\$ or US- 6455340-\$ or US- 7151281-\$ or US- 4696648-\$ or US- 4593304-\$ or US- 7002189-\$ or US- 7329908-\$ or US- 7285806-\$ or US- 7224004-\$ or US- 7205168-\$ or US- 7132699-\$ or US- 7071526-\$ or US- 6969873-\$ or US- 6965107-\$).did. or (US-6890834-\$ or US- 6703649-\$ or US- 6593597-\$ or US- 6552373-\$ or US- 6492669-\$ or US- 6350999-\$ or US- 6064082-\$ or US- 7229866-\$ or US- 7115896-\$ or US- 7253015-\$).did. or (JP-06216404-\$ or JP- 01253286-\$ or JP- 2004228481-\$ or JP- 2003229566-\$ or JP- 2000223697-\$).did. or (US-20050012113-\$ or US-20030230235-\$ or EP-296371-\$ or US- 20050032345-\$ or JP- 06216404-\$ or KR- 587021-B-\$ or KR- 609968-B-\$ or CN- 1641327-\$ or US- 20040080011-A-\$ or JP-2001185717-\$ or WO-03094240-A-\$). did.				
L122	4	l121 and (schottky near contact) near2 between	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:02
L123	9	l121 and (schottky near contact) near5 between	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:03

L124	76	l121 and (schottky near contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:11
L125	33	l121 and ((form or forming or formed or formation) near2 (schottky near contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:12
L126	41	l121 and ((form or forming or formed or formation) near5 (schottky near contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:14
L127	3616	257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:44
L128	103	l127 and (schottky near2 diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:44
L129	103	l127 and ((schottky near2 diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:44
L130	5056	257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls. or 257/194.ccls. or 438/604.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:45
L131	166	l130 and ((schottky near2 diode) or sbd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/10 19:45

3/10/08 7:45:55 PM

C:\Documents and Settings\FERdem\My Documents\EAST\workspaces\10707084_case.wsp